

## Silicon NPN Power Transistors

## 2SC1450

## DESCRIPTION

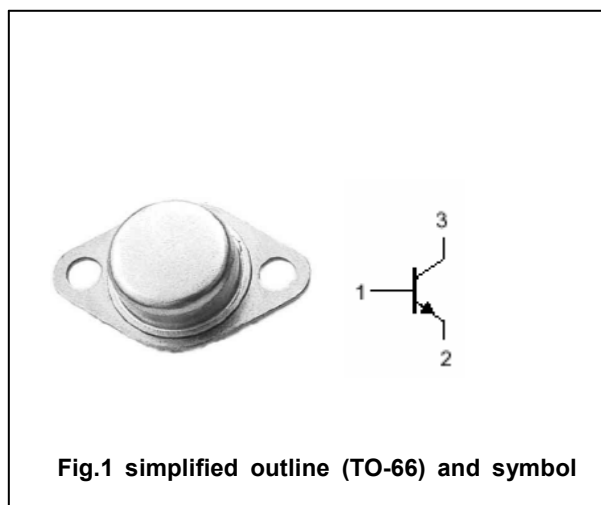
- With TO-66 package
- Wide area of safe operation
- High collector-emitter breakdown voltage  
:V<sub>CEO</sub>=150V(min)
- Complement to type 2SA766

## APPLICATIONS

- For power amplifier and vertical output applications.

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings(T<sub>a</sub>=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	150	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		0.4	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =80□	20	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-65~200	□

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =30mA; I <sub>B</sub> =0	150			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA; I <sub>E</sub> =0	150			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =0.5A; I <sub>B</sub> =50m A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =150V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	30		150	

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PACKAGE OUTLINE



Fig.2 outline dimensions